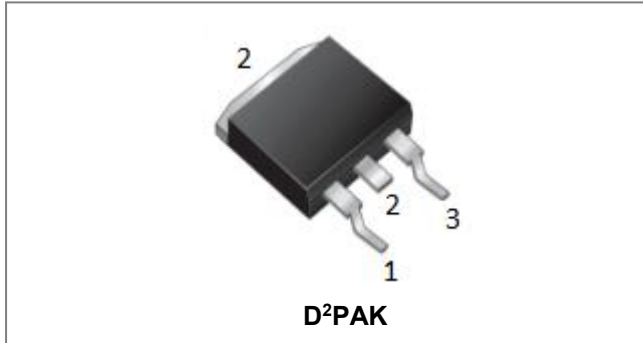


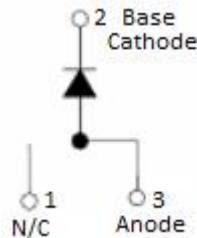
SDURB8U120 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings (limiting values, TC =25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_F (AV)$	50% duty cycle @Tc=70°C, rectangular wave form	8	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	80	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 8A, Pulse, T _J = 25°C	1.85	2.20	V
	V_{F2}	@ 8A, Pulse, T _J = 125°C	1.63	2.00	V
Reverse Current*	I_{R1}	@V _R = rated V _R , T _J =25°C	0.005	10	uA
	I_{R2}	@V _R = rated V _R , T _J =125°C	0.2	1	mA
Reverse Recovery Time	t _{rr}	I _F =500mA, I _R =1A, and I _{rm} =250mA	41	50	ns

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	1.5	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

Ratings and Characteristics Curves

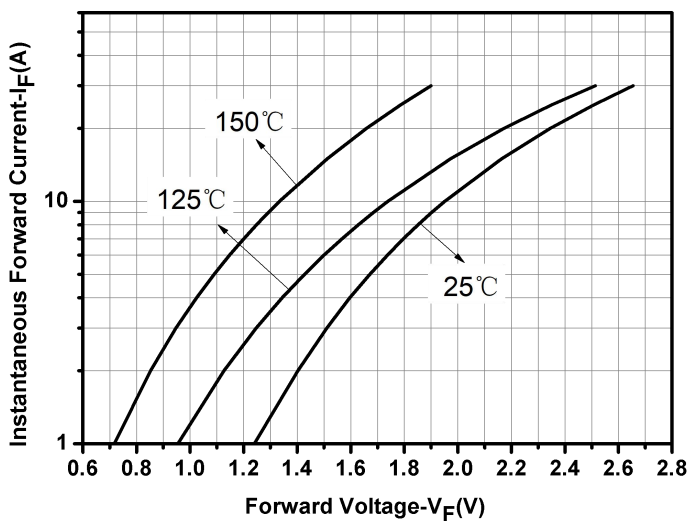


Fig.1-Typical Forward Voltage Characteristics

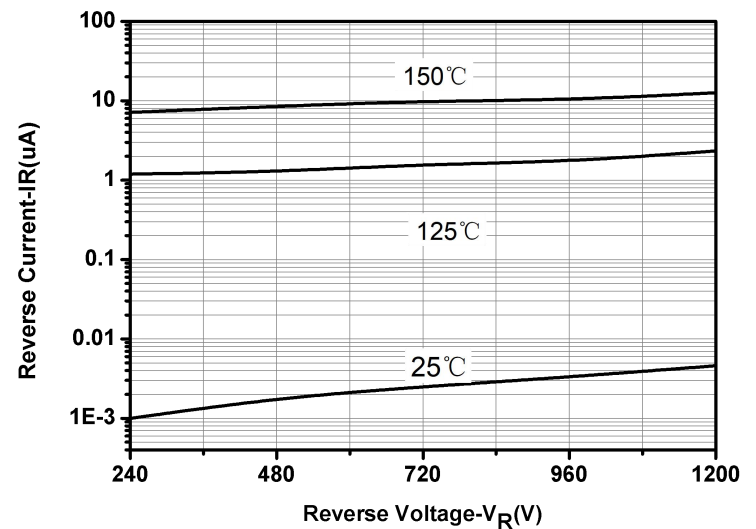


Fig.2-Typical Reverse Characteristics

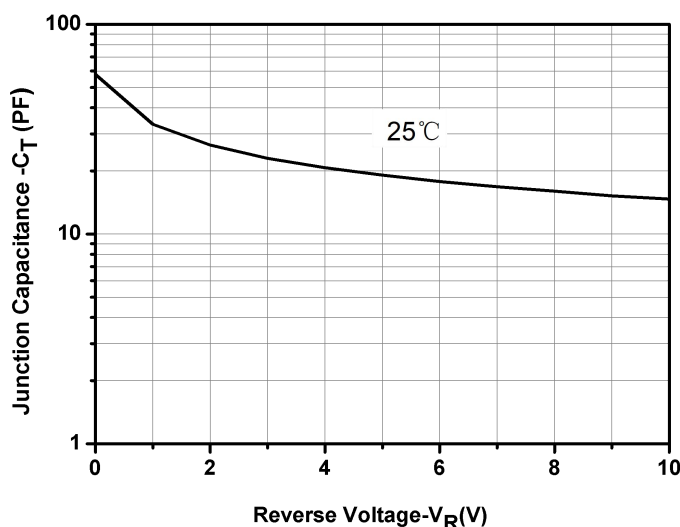


Fig.3-Capacitance vs. Reverse Voltage

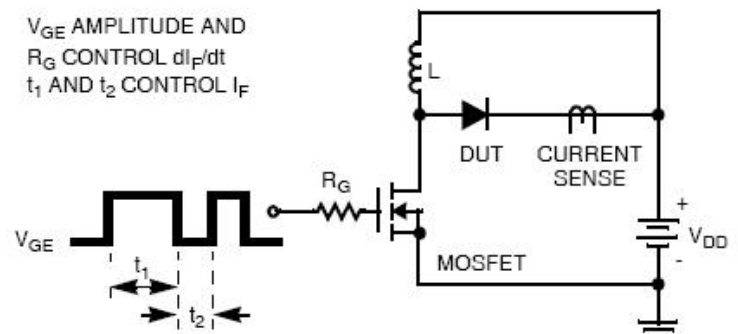
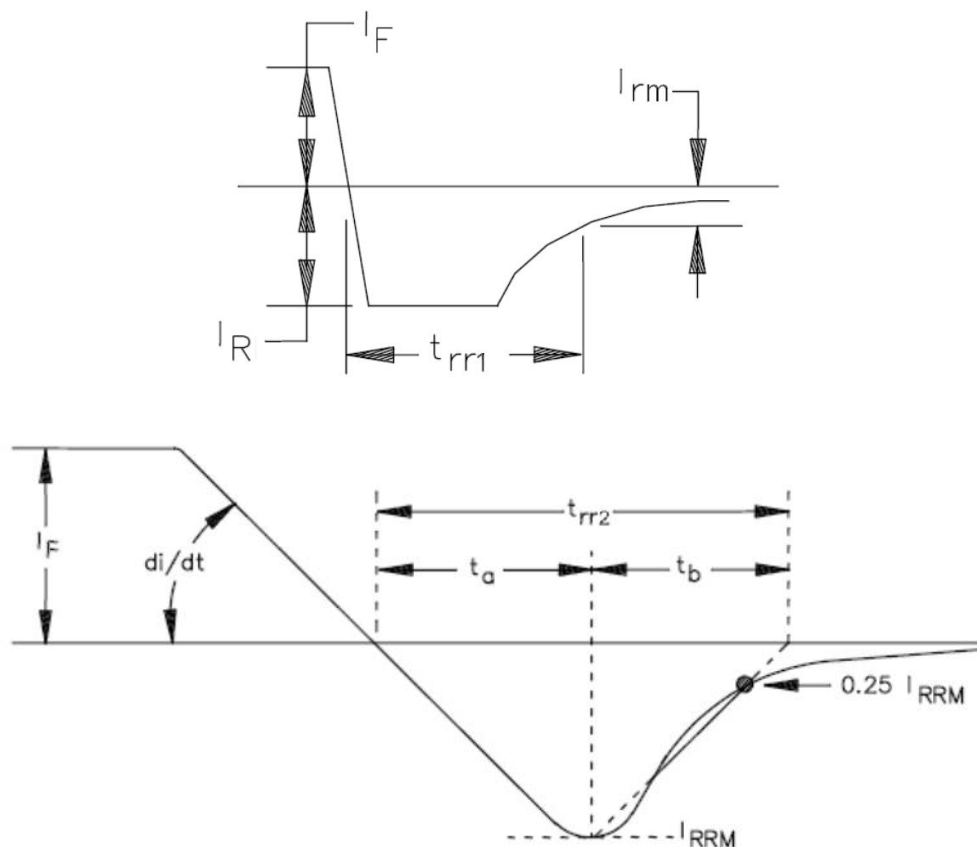
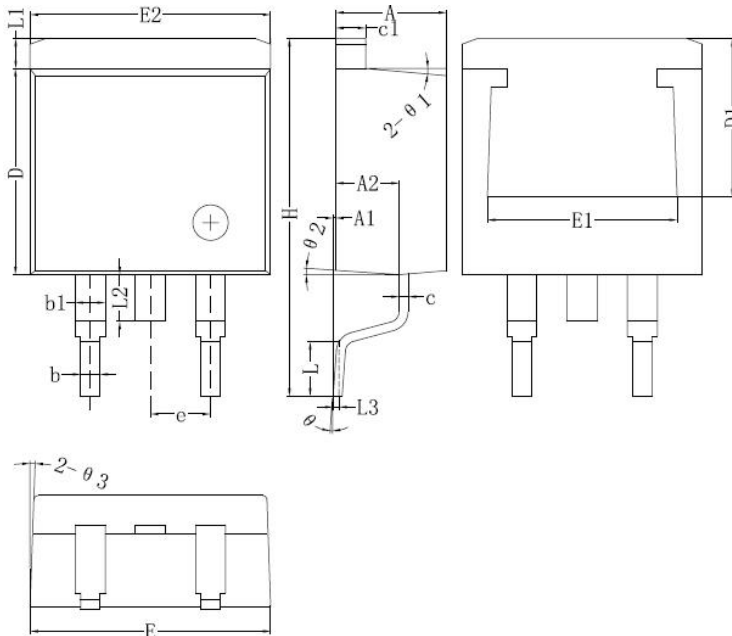


Fig.4-Diode Test Circuit



Note: 1. t_{rr1} MIL-STD-750 Test Method 4031, condition "B".
2. t_{rr2} MIL-STD-750 Test Method 4031, condition "D".

Fig.5-Reverse Recovery Waveform

Mechanical Dimensions D²PAK


Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	9.65
D1	6.4	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.6	15.88
L	1.78	2.8
L1	-	1.68
L2	-	2.2
L3	0.255BSC	
Θ	0	8°

Ordering Information

Device	Package	Shipping
SDURB8U120	D ² PAK	800pcs / reel
SDURB8U120TR	D ² PAK	800pcs / reel

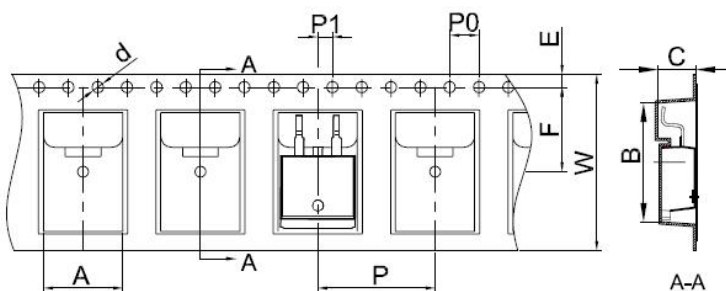
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Where XXXXX is YYWWL

SDUR = Device Type
 B = Package type
 8 = Forward Current (8A)
 U = U
 120 = Reverse Voltage(1200V)
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK


SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

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